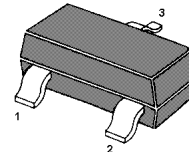


MMBT9013H-H23

NPN Silicon Epitaxial Planar Transistors

for switching and amplifier applications.

As complementary types the PNP transistor MMBT9012 is recommended.



1. Base 2. Emitter 3. Collector
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CB0}	40	V
Collector Emitter Voltage	V_{CE0}	30	V
Emitter Base Voltage	V_{EB0}	5	V
Collector Current	I_C	500	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $V_{CE} = 1\text{ V}$, $I_C = 50\text{ mA}$	h_{FE}	200	300	-
Collector Base Cutoff Current at $V_{CB} = 35\text{ V}$	I_{CB0}	-	100	nA
Emitter Base Cutoff Current at $V_{EB} = 5\text{ V}$	I_{EB0}	-	100	nA
Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	$V_{(BR)CB0}$	40	-	V
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CE0}$	30	-	V
Emitter Base Breakdown Voltage at $I_E = 100\text{ }\mu\text{A}$	$V_{(BR)EB0}$	5	-	V
Collector Emitter Saturation Voltage at $I_C = 500\text{ mA}$, $I_B = 50\text{ mA}$	$V_{CE(sat)}$	-	0.6	V
Base Emitter Saturation Voltage at $I_C = 500\text{ mA}$, $I_B = 50\text{ mA}$	$V_{BE(sat)}$	-	1.2	V
Base Emitter Voltage at $V_{CE} = 1\text{ V}$, $I_C = 100\text{ mA}$	V_{BE}	-	1	V
Gain Bandwidth Product at $V_{CE} = 6\text{ V}$, $I_C = 20\text{ mA}$	f_T	100	-	MHz

